Application Note

March 17, 2009

AN1458.0

ISL7457SRH TID Rating

The ISL7457SRH is specified for 10krads(Si) minimum TID in SMD 5962-08230 when continuously biased as shown in Figure 1.

In many cases a 10krad(Si) TID rating is not adequate to meet mission requirements, so a method to extend the TID capability is desired. Figure 2 shows a radiation exposure circuit that biases the ISL7457SRH only 20% of the time. For the other 80% of the time, the ISL7457SRH is unbiased. Devices irradiated in this manner have demonstrated acceptable post-rad parametric limits after 50krad(Si) TID, as indicated in the Electrical Specification tables of this application note. Please note, however, that the post-50krad electrical specifications shown herein are not specified in or guaranteed by SMD 5962-08230.

Imaging Applications

Some camera CCD driver applications do not require 100% availability. In these situations, the ISL7457SRH can be left unbiased until there is a need to image. When imaging is required, the ISL7457SRH can be quickly biased by simply closing a switch. As long as the duty-cycle of the application does not exceed 20%, the TID capability can be extended up to 50krad(Si).

Conclusions

A simple method to extend the TID capability of the ISL7457SRH to 50krad(Si) has been described. This method can be applied to any space-based system that uses the device as long as 20% availability is acceptable.

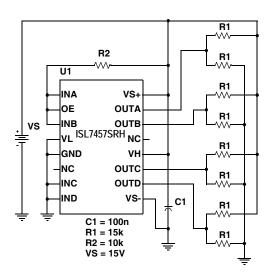


FIGURE 1. RAD EXPOSURE CIRCUIT (BIAS DUTY CYCLE = 100%)

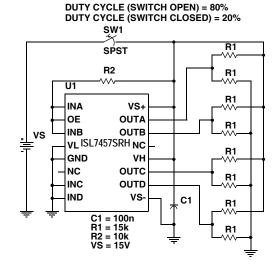


FIGURE 2. RAD EXPOSURE CIRCUIT (BIAS DUTY CYCLE = 20%)

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 $\begin{tabular}{ll} \textbf{Electrical Specifications} & V_S+=V_H=5V\ \pm 10\%,\ V_{S^-}=V_L=0V,\ OE=V_S+,\ T_A=\pm 25^\circ C,\ Post\ 50krad(Si)\ unless\ otherwise\ specified.\ Refer to\ Figure\ 2\ for\ radiation\ exposure\ circuit\ biasing. \end{tabular}$

PARAMETER	DESCRIPTION	CONDITION	MIN	TYP	MAX	UNIT
INPUT	<u>'</u>		Į.	U.	U.	1
V _{IH}	Logic "1" Input Voltage		2			V
I _{IH}	Logic "1" Input Current	$INx = V_S +$	-10		10	μA
V _{IL}	Logic "0" Input Voltage				0.6	V
I _{IL}	Logic "0" Input Current	INx = 0V	-10		10	μA
OUTPUT			1	•		
R _{OH}	ON Resistance V _H to OUTx	INx = V _S +, I _{OUTx} = -100mA			12	Ω
R _{OL}	ON Resistance V _L to OUTx	INx = 0V, I _{OUTx} = +100mA			7	Ω
I _{LEAK+}	Positive Output Leakage Current	$INx = V_S+$, $OE = 0V$, $OUTx = V_S+$			300	μΑ
I _{LEAK} -	Negative Output Leakage Current	$INx = V_S+$, $OE = 0V$, $OUTx = V_S-$	-50			μΑ
POWER SUPPL	.Y	,				
I _{S+}	V _S + Supply Current	INx = 0V and V _S +			5	mA
I _S -	V _S - Supply Current	INx = 0V and V _S +	-5			mA
I _H	V _H Supply Current	INx = 0V and V _S +			650	μΑ
IL	V _L Supply Current	INx = 0V and V _S +	-650			μΑ
SWITCHING CH	HARACTERISTICS	,	J.			
t _R	Rise Time	INx = 0V to 4.5V step, C _L = 1nF			40	ns
t _F	Fall Time	$INx = 4.5V \text{ to } 0V \text{ step, } C_L = 1nF$			26	ns
$t_{RF\Delta}$	t _R , t _F Mismatch	C _L = 1nF			5	ns
t _D +	Turn-On Delay Time	INx = 0V to 4.5V step, C _L = 1nF			30	ns
t _D -	Turn-Off Delay Time	$INx = 4.5V \text{ to } 0V \text{ step, } C_L = 1nF$			40	ns
t _{DD}	t _D +, t _D - Mismatch	C _L = 1nF			12	ns
t _{ENABLE}	Enable Delay Time	INx = V _S +, OE = 0V to 4.5V step, $R_L = 1k\Omega$			35	ns
^t DISABLE	Disable Delay Time	INX = V_S +, OE = 4.5V to 0V step, R_L = 1k Ω			50	ns

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Electrical Specifications

 V_S + = V_H = 15V ±10%, V_S - = V_L = 0V, OE = V_S +, T_A = +25°C, Post 50krad(Si) unless otherwise specified. Refer to Figure 2 for radiation exposure circuit biasing.

PARAMETER	DESCRIPTION	CONDITION	MIN	TYP	MAX	UNIT
INPUT		·				
V _{IH}	Logic "1" Input Voltage		2			V
I _{IH}	Logic "1" Input Current	$INx = V_S +$	-10		10	μΑ
V _{IL}	Logic "0" Input Voltage				0.6	V
I _{IL}	Logic "0" Input Current	INx = 0V	-10		10	μA
OUTPUT						
R _{OH}	ON Resistance V _H to OUTx	$INx = V_S+$, $I_{OUTx} = -100mA$			5	Ω
R _{OL}	ON Resistance V _L to OUTx	INx = 0V, I _{OUTx} = +100mA			5	Ω
I _{LEAK+}	Positive Output Leakage Current	$INx = V_S+$, $OE = 0V$, $OUTx = V_S+$			300	μA
I _{LEAK} -	Negative Output Leakage Current	$INx = V_S+$, $OE = 0V$, $OUTx = V_S-$	-50			μΑ
POWER SUPPL	Y	·				,
I _{S+}	V _S + Supply Current	INx = 0V and V _S +			5	mA
I _S -	V _S - Supply Current	INx = 0V and V _S +	-5			mA
I _H	V _H Supply Current	INx = 0V and V _S +			750	μA
IL	V _L Supply Current	INx = 0V and V _S +	-750			μA
SWITCHING CH	IARACTERISTICS	•		•		
t _R	Rise Time	INx = 0V to 5V step, C _L = 1nF			20	ns
t _F	Fall Time	INx = 5V to 0V step, C _L = 1nF			20	ns
$t_{RF\Delta}$	t _R , t _F Mismatch	C _L = 1nF			3	ns
t _D +	Turn-On Delay Time	INx = 0V to 5V step, C _L = 1nF			20	ns
t _D -	Turn-Off Delay Time	INx = 5V to 0V step, C _L = 1nF			20	ns
t _{DD}	t _D +, t _D - Mismatch	C _L = 1nF			5	ns
t _{ENABLE}	Enable Delay Time	INx = V_S +, OE = 0V to 5V step, R_L = 1k Ω			25	ns
t _{DISABLE}	Disable Delay Time	INx = V_S +, OE = 5V to 0V step, R_L = $1k\Omega$			65	ns

Intersil Corporation reserves the right to make changes in circuit design, software and/or specifications at any time without notice. Accordingly, the reader is cautioned to verify that the Application Note or Technical Brief is current before proceeding.